ALPHA & OMEGA SEMICONDUCTOR

AOU405
P-Channel Enhancement Mode Field Effect Transistor

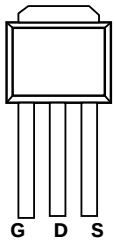
General Description

The AOU405 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and low gate resistance. With the excellent thermal resistance of the TO-251 package, this device is well suited for high current load applications. *Standard Product AOU405 is Pb-free (meets ROHS & Sony 259 specifications). AOU405L is a Green Product ordering option. AOU405 and AOU405L are electrically identical.*

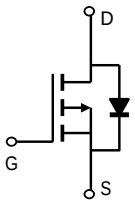
Features

V_{DS} (V) = -30V
I_D = -18A (V_{GS} = -10V)
$R_{DS(ON)}$ < 34mΩ (V_{GS} = -10V)
$R_{DS(ON)}$ < 60mΩ (V_{GS} = -4.5V)

TO-251



Top View
Drain Connected
to Tab



Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [B,G]	T_A=25°C [G]	I_D	-18	A
	T_A=100°C [G]		-18	
Pulsed Drain Current		I_{DM}	-40	
Avalanche Current [C]		I_{AR}	-18	A
Repetitive avalanche energy L=0.1mH [C]		E_{AR}	40	mJ
Power Dissipation [B]	T_C=25°C	P_D	60	W
	T_C=100°C		30	
Power Dissipation [A]	T_A=25°C	P_{DSM}	2.5	W
	T_A=70°C		1.6	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 175	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	16.7	25	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		40	50	°C/W
Maximum Junction-to-Case [C]	Steady-State	$R_{\theta JC}$	1.8	2.5	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-24V, V_{GS}=0V		-0.003	-1	µA
		T_J=55°C			-5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±20V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=-250µA	-1.2	-2	-2.4	V
$I_{D(ON)}$	On state drain current	V_{GS}=-10V, V_{DS}=-5V	-40			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V, I_D=-18A		28	34	mΩ
		T_J=125°C		40	47	
		V_{GS}=-4.5V, I_D=-10A		48	60	mΩ
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-18A		17		S
V_{SD}	Diode Forward Voltage	I_S=-1A,V_{GS}=0V		-0.76	-1	V
I_S	Maximum Body-Diode Continuous Current				-18	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-15V, f=1MHz		920	1100	pF
C_{oss}	Output Capacitance			190		pF
C_{rss}	Reverse Transfer Capacitance			122		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		3.6	4.5	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge (10V)	V_{GS}=-10V, V_{DS}=-15V, I_D=-18A		18.7	23	nC
Q_g(4.5V)	Total Gate Charge (4.5V)			9.7	11.7	nC
Q_{gs}	Gate Source Charge			2.54		nC
Q_{gd}	Gate Drain Charge			5.4		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-10V, V_{DS}=-15V, R_L=0.82Ω, R_{GEN}=3Ω		9	13	ns
t_r	Turn-On Rise Time			25	35	ns
$t_{D(off)}$	Turn-Off DelayTime			20	30	ns
t_f	Turn-Off Fall Time			12	18	ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-18A, dI/dt=100A/µs		21.4	26	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-18A, dI/dt=100A/µs		13	16	nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in ^{2} FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C. The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

B. The power dissipation P_D is based on $T_{J(MAX)}$=175°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=175°C.

D. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to case $R_{\theta JC}$ and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 µs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedence which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=175°C.

G. The maximum current rating is limited by bond-wires.

H. These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

I. Revision 0: August 2005

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

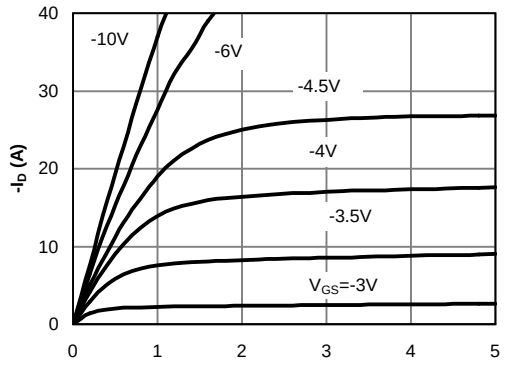


Fig 1: On-Region Characteristics

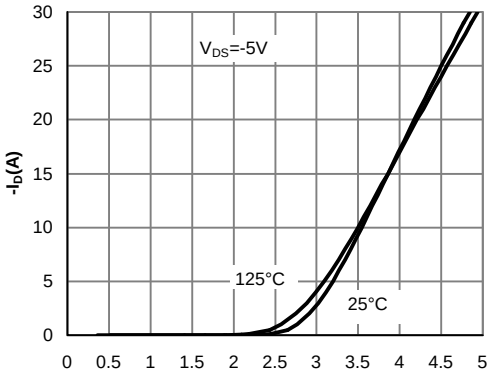


Figure 2: Transfer Characteristics

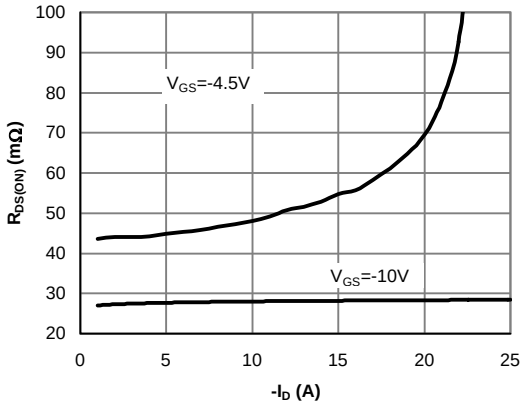


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

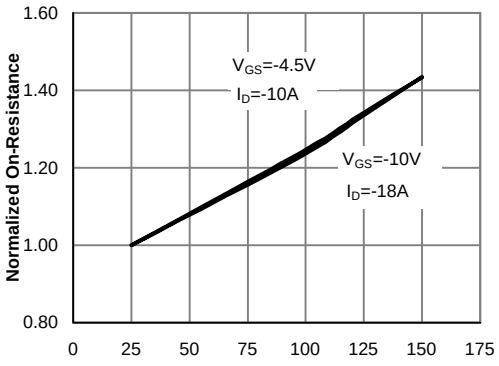


Figure 4: On-Resistance vs. Junction Temperature

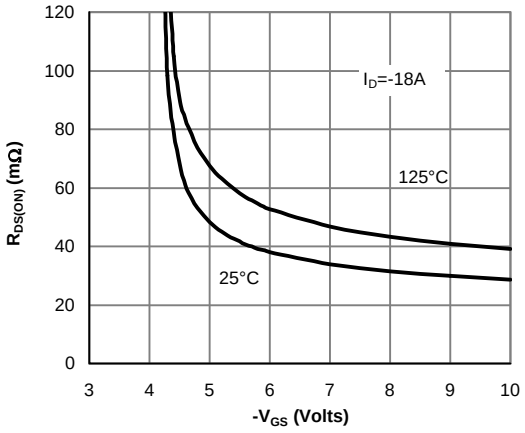


Figure 5: On-Resistance vs. Gate-Source Voltage

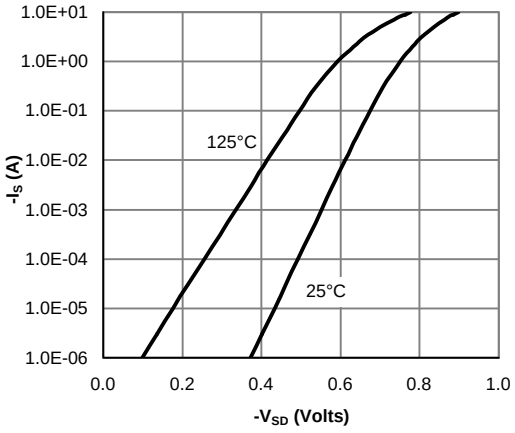


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

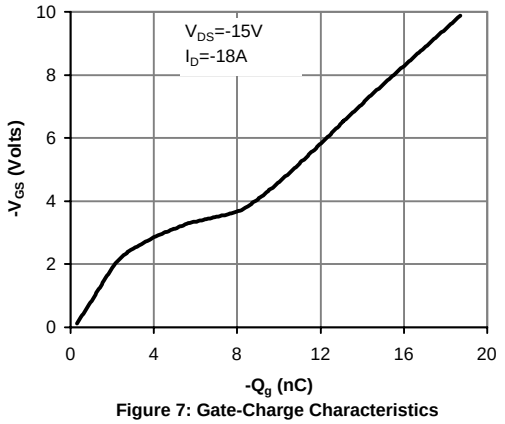


Figure 7: Gate-Charge Characteristics

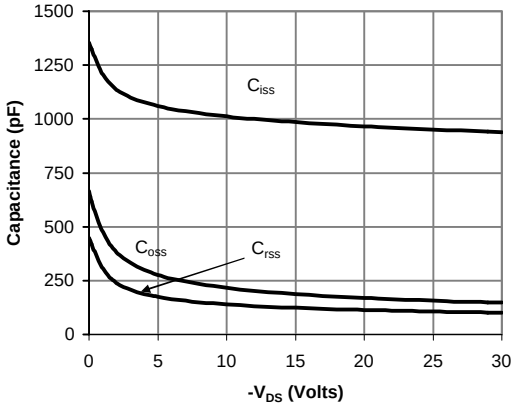


Figure 8: Capacitance Characteristics

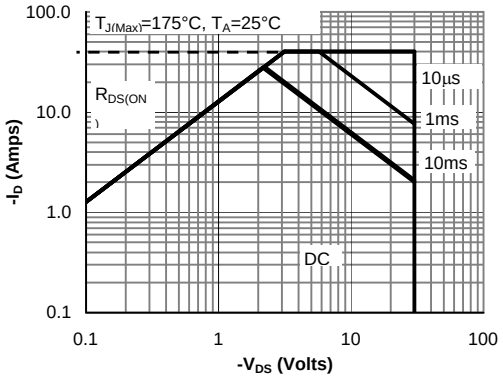


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

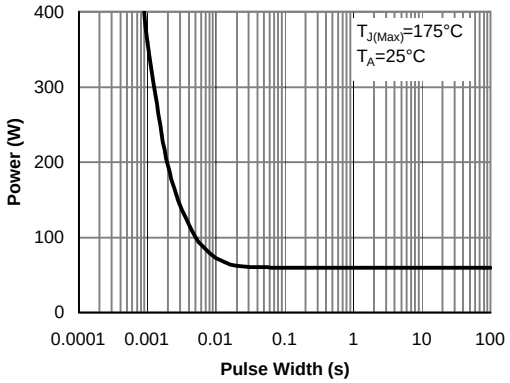


Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

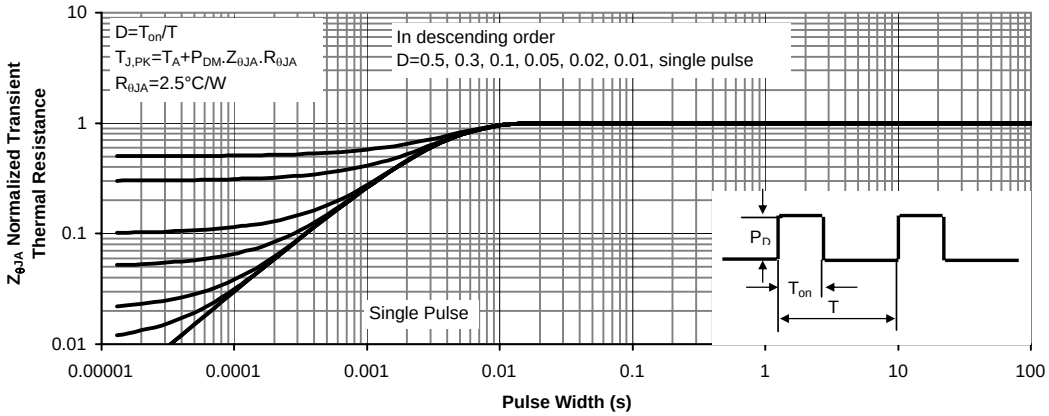


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

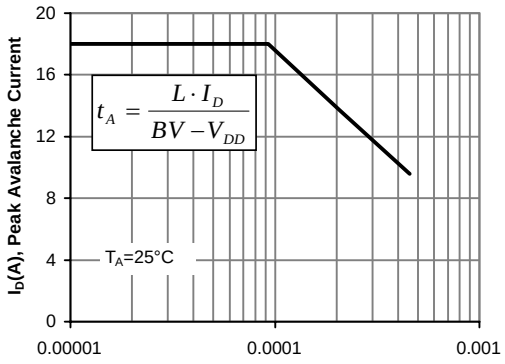


Figure 12: Single Pulse Avalanche capability

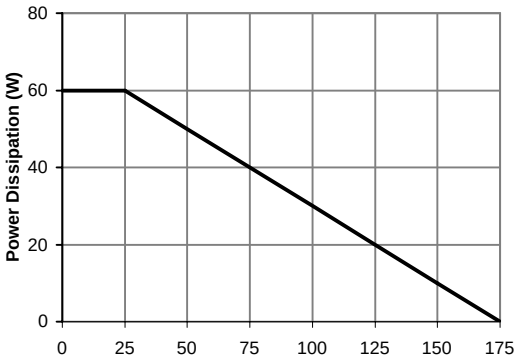


Figure 13: Power De-rating (Note B)

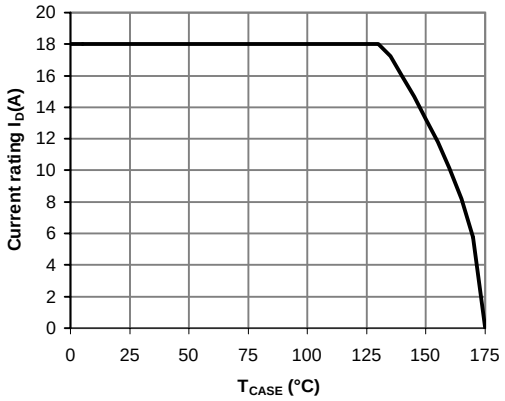


Figure 14: Current De-rating (Note B)